MC100LVELT22

3.3V Dual LVTTL/LVCMOS to Differential LVPECL Translator

Description

The MC100LVELT22 is a dual LVTTL/LVCMOS to differential LVPECL translator. Due to LVPECL (Low Voltage Positive ECL) levels, only +3.3V and ground is required. The small 8−lead package outline with low skew dual gate design makes the MC100LVELT22 ideal for applications which require translation of a clock and/or data signal.

Features

- 350 ps Typical Propagation Delay
- <100 ps Output−to−Output Skew
- Flow Through Pinouts
- The 100 Series Contains Temperature Compensation
- LVPECL Operating Range: V_{CC} = 3.15 V to 3.45 V with GND = 0 V
- When Unused TTL Input is left Open, Q Output will Default High
- These are Pb−Free Devices

ON Semiconductor®

MARKING DIAGRAMS*

8 SOIC−8
D SUFFIX
CASE 751

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KVT22
ALYW
```

8 TSSOP−8
DT SUFFIX
CASE 948R

```
KR22
ALYW■
```
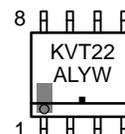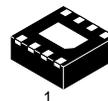
1 DFN8
MN SUFFIX
CASE 506AA

```
M
41
```
1   4

A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
$\overline{M}$ = Date Code
■ = Pb−Free Package

(Note: Microdot may be in either location)

*For additional marking information, refer to Application Note AND8002/D.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MC100LVELT22

Q0 1 [▷] 8 V_CC
$\overline{Q0}$ 2 7 D0

LVPECL **LVTTL/ LVCMOS**

Q1 3 [▷] 6 D1
$\overline{Q1}$ 4 5 GND

Figure 1. 8–Lead Pinout (Top View) **and Logic Diagram**
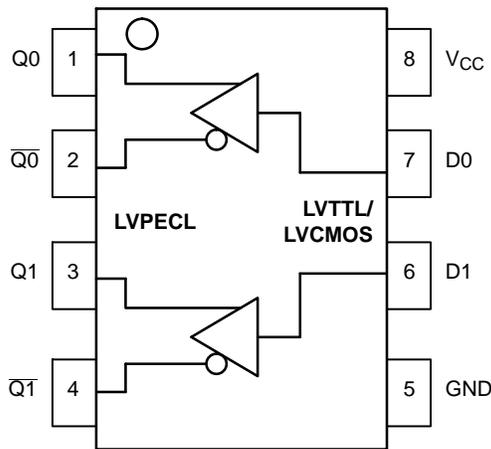
Table 1. PIN DESCRIPTION

PIN	FUNCTION
Qn, $\overline{Qn}$	LVPECL Differential Outputs
D0, D1	LVTTL/LVCMOS Inputs
V_CC	Positive Supply
GND	Ground
EP	(DFN8 only) Thermal exposed pad must be connected to a sufficient thermal conduit. Electrically connect to the most negative supply (GND) or leave unconnected, floating open.

Table 2. ATTRIBUTES

Characteristics		Value
Internal Input Pulldown Resistor		N/A
Internal Input Pullup Resistor		N/A
ESD Protection	Human Body Model Machine Model	> 4 kV > 200 V
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)		Level 1
Flammability Rating	Oxygen Index: 28 to 34	UL 94 V–0 @ 0.125 in
Transistor Count		164
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test		

1. For additional information, see Application Note AND8003/D.

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V_CC	Positive Power Supply	GND = 0 V		7	V
V_I	Input Voltage	GND = 0 V	$V_I \leq V_{CC}$	7	V
I_out	Output Current	Continuous Surge		50 100	mA mA
T_A	Operating Temperature Range			−40 to +85	°C
T_stg	Storage Temperature Range			−65 to +150	°C
θ_{JA}	Thermal Resistance (Junction–to–Ambient)	0 lfpm 500 lfpm	SO–8 SO–8	190 130	°C/W °C/W
θ_{JC}	Thermal Resistance (Junction–to–Case)	std bd	SO–8	41 to 44 ± 5%	°C/W
θ_{JA}	Thermal Resistance (Junction–to–Ambient)	0 lfpm 500 lfpm	TSSOP–8 TSSOP–8	185 140	°C/W °C/W
θ_{JC}	Thermal Resistance (Junction–to–Case)	std bd	TSSOP–8	41 to 44 ± 5%	°C/W
θ_{JA}	Thermal Resistance (Junction–to–Ambient)	0 lfpm 500 lfpm	DFN8 DFN8	129 84	°C/W °C/W
T_sol	Wave Solder Pb Pb–Free	<2 to 3 sec @ 248°C <2 to 3 sec @ 260°C		265 265	°C
θ_{JC}	Thermal Resistance (Junction–to–Case)	(Note 2)	DFN8	35 to 40	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
2. JEDEC standard multilayer board – 2S2P (2 signal, 2 power)

Table 4. LVPECL DC CHARACTERISTICS V_{CC} = 3.3 V; GND = 0.0 V (Note 3)

Symbol	Characteristic	−40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{CC}	Power Supply Current			28			28			29	mA
V_{OH}	Output HIGH Voltage (Note 4)	2275		2420	2275		2420	2275		2420	mV
V_{OL}	Output LOW Voltage (Note 4)	1490		1680	1490		1680	1490		1680	mV

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.
3. Output parameters vary 1:1 with V_{CC}. V_{CC} can vary ±0.15 V.
4. Outputs are terminated through a 50 ohm resistor to V_{CC}−2 V.

Table 5. LVTTL/LVCMOS INPUT DC CHARACTERISTICS V_{CC} = 3.3 V; T_A = −40°C to 85°C (Note 5)

Symbol	Characteristic	Min	Typ	Max	Unit	Condition
I_{IH}	Input HIGH Current			20	μA	V_{IN} = 2.7 V
I_{IHH}	Input HIGH Current			100	μA	V_{IN} = V_{CC}
I_{IL}	Input LOW Current			−0.2	mA	V_{IN} = 0.5 V
V_{IK}	Input Clamp Diode Voltage			−1.2	V	I_{IN} = −18 mA
V_{IH}	Input HIGH Voltage	2.0			V	
V_{IL}	Input LOW Voltage			0.8	V	

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.
5. V_{CC} can vary ±0.15 V.

Table 6. AC CHARACTERISTICS V_{CC} = 3.3 V; GND = 0.0 V (Note 6)

Symbol	Characteristic	−40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
f_{max}	Maximum Toggle Frequency					350					MHz
t_{PLH}	Propagation Delay (Note 7)	200	350	600	200	350	600	200	350	600	ps
t_{skew}	Skew Output−to−Output Part−to−Part		30	100 400		30	100 400		30	100 400	ps
t_{JITTER}	Random Clock Jitter (RMS)			2.1		1.1	1.9			1.6	ps
$t_{jit(\phi)}$	Additive RMS Phase Jitter f_c = 50 MHz, Integration Range: 12 kHz to 20 MHz (See Figure 2)					219					fs
t_r/t_f	Output Rise/Fall Time (20−80%)	200		550	200		500	200		500	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.
6. V_{CC} can vary ±0.15 V. Outputs are terminated through a 50 Ω resistor to V_{CC} − 2 V.
7. Specifications for standard TTL input signal.
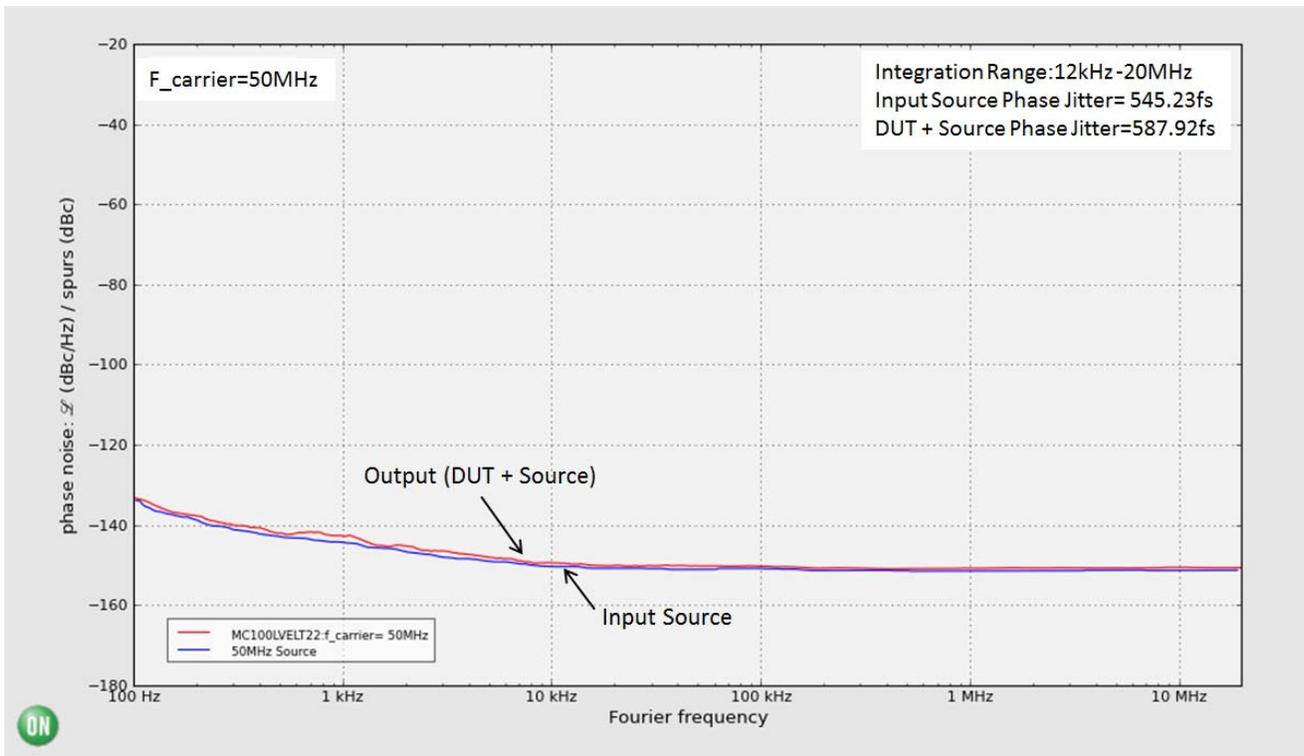
**Figure 2. Typical MC100LVELT22 Phase Noise Plot at $f_{Carrier}$ = 50 MHz, V_{CC} = 3.3 V, 25°C**

The above phase noise data was captured using Agilent E5052A/B. The data displays the input phase noise and output phase noise used to calculate the additive phase jitter at a specified integration range. The additive RMS phase jitter contributed by the device (integrated between 12 kHz and 20 MHz) is 219 fs. The additive RMS phase jitter performance of the translator is highly dependent on the phase noise of the input source.

To obtain the most precise additive phase noise measurement, it is vital that the source phase noise be notably lower than that of the DUT. If the phase noise of the source is greater than the noise floor of the device under test, the source noise will dominate the additive phase jitter calculation and lead to an incorrect negative result for the additive phase noise within the integration range. The Figure above is a good example of the MC100LVELT22 source generator phase noise having a significantly lower floor than the DUT and results in an additive phase jitter of 219 fs.

$$\text{Additive RMS phase jitter} = \sqrt{\text{RMS phase jitter of output}^2 - \text{RMS phase jitter of input}^2}$$

$$219 \text{ fs} = \sqrt{587.92 \text{ fs}^2 - 545.23 \text{ fs}^2}$$

Figure 2 was created with measured data from Agilent–E5052B Signal Source Analyzer using ON Semiconductor Phase Noise Explorer web tool. This free application enables an interactive environment for advanced phase noise and jitter analysis of timing devices and clock tree designs. To see the performance of MC100LVELT22 beyond conditions outlined in this datasheet, please visit the ON Semiconductor Green Point Design Tools homepage.

$V_{TT} = V_{CC} - 2.0 V$
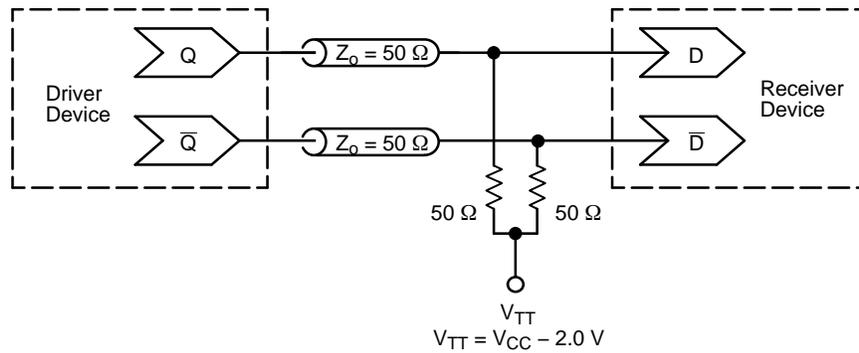
Figure 3. Typical Termination for Output Driver and Device Evaluation
(See Application Note AND8020/D – Termination of ECL Logic Devices.)

ORDERING INFORMATION

Device	Package	Shipping[†]
MC100LVELT22DG	SOIC−8 (Pb−Free)	98 Units / Rail
MC100LVELT22DR2G	SOIC−8 (Pb−Free)	2500 / Tape & Reel
MC100LVELT22DTG	TSSOP−8 (Pb−Free)	100 Units / Rail
MC100LVELT22DTRG	TSSOP−8 (Pb−Free)	2500 / Tape & Reel
MC100LVELT22MNRG	DFN8 (Pb−Free)	1000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Resource Reference of Application Notes

AN1405/D – ECL Clock Distribution Techniques

AN1406/D – Designing with PECL (ECL at +5.0 V)

AN1503/D – ECLinPS™ I/O SPiCE Modeling Kit

AN1504/D – Metastability and the ECLinPS Family

AN1568/D – Interfacing Between LVDS and ECL

AN1672/D – The ECL Translator Guide

AND8001/D – Odd Number Counters Design

AND8002/D – Marking and Date Codes

AND8020/D – Termination of ECL Logic Devices

AND8066/D – Interfacing with ECLinPS

AND8090/D – AC Characteristics of ECL Devices

PACKAGE DIMENSIONS

SOIC−8 NB
CASE 751−07
ISSUE AK
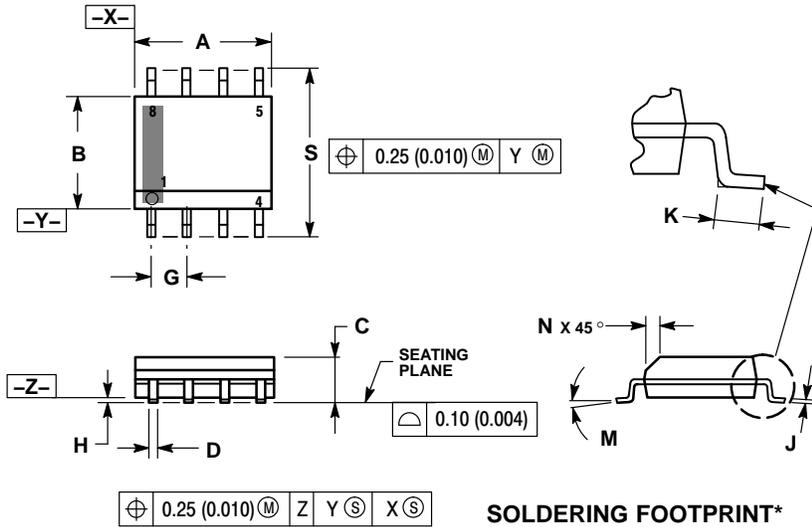
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751−01 THRU 751−06 ARE OBSOLETE. NEW STANDARD IS 751−07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*

$\frac{1.52}{0.060}$

$\frac{7.0}{0.275}$

$\frac{4.0}{0.155}$

$\frac{0.6}{0.024}$

$\frac{1.270}{0.050}$
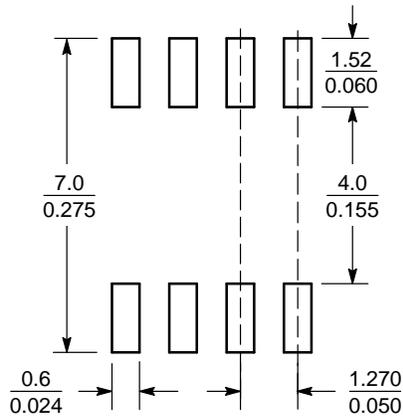
SCALE 6:1 $\left(\frac{mm}{inches}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MC100LVELT22

## PACKAGE DIMENSIONS

TSSOP–8
DT SUFFIX
CASE 948R–02
ISSUE A
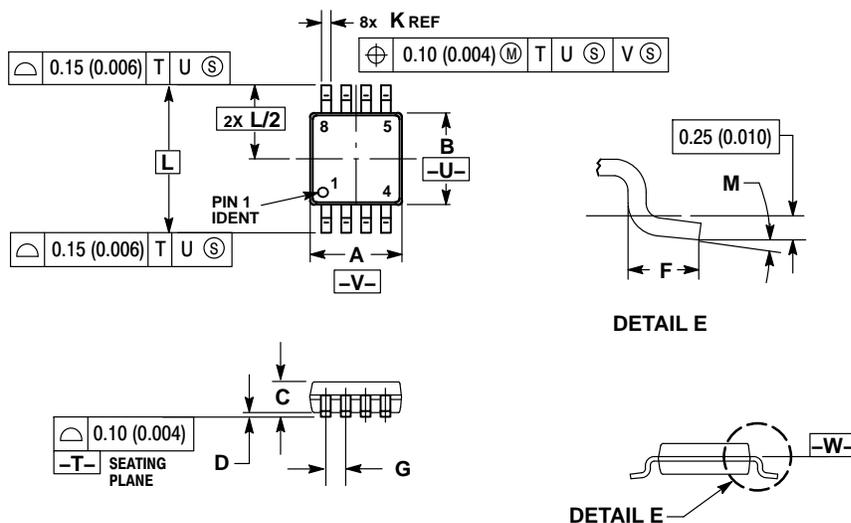
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
6. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

DETAIL E

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.90	3.10	0.114	0.122
B	2.90	3.10	0.114	0.122
C	0.80	1.10	0.031	0.043
D	0.05	0.15	0.002	0.006
F	0.40	0.70	0.016	0.028
G	0.65 BSC		0.026 BSC	
K	0.25	0.40	0.010	0.016
L	4.90 BSC		0.193 BSC	
M	0 °	6 °	0 °	6 °

MC100LVELT22

PACKAGE DIMENSIONS

DFN8 2x2, 0.5P
CASE 506AA
ISSUE E

TOP VIEW

2X | 0.10 | C
2X | 0.10 | C

PIN ONE REFERENCE

DETAIL A
OPTIONAL CONSTRUCTIONS

L1 | L | L

SIDE VIEW

0.10 | C
0.08 | C
NOTE 4

DETAIL B
(A3)
A1
A
C SEATING PLANE

DETAIL B
OPTIONAL CONSTRUCTION

EXPOSED Cu   MOLD CMPD
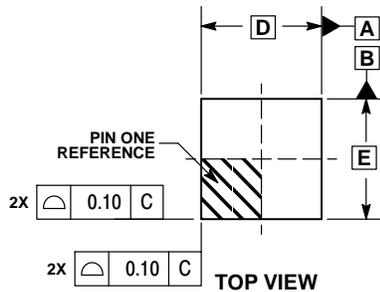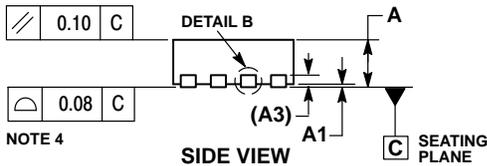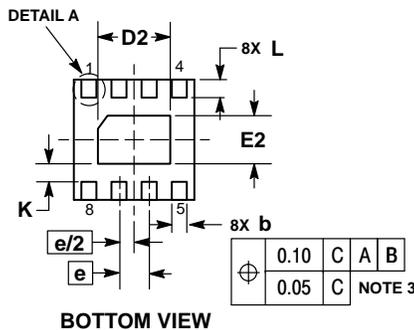
BOTTOM VIEW

DETAIL A
D2
8X L
E2
K
e/2
e
8X b
0.10 | C | A | B
0.05 | C | NOTE 3

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994 .
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

DIM	MILLIMETERS MIN	MILLIMETERS MAX
A	0.80	1.00
A1	0.00	0.05
A3	0.20 REF	
b	0.20	0.30
D	2.00 BSC	
D2	1.10	1.30
E	2.00 BSC	
E2	0.70	0.90
e	0.50 BSC	
K	0.30 REF	
L	0.25	0.35
L1	–––	0.10

RECOMMENDED SOLDERING FOOTPRINT*

PACKAGE OUTLINE
1.30
0.90
8X 0.30
8X 0.50
2.30
0.50 PITCH
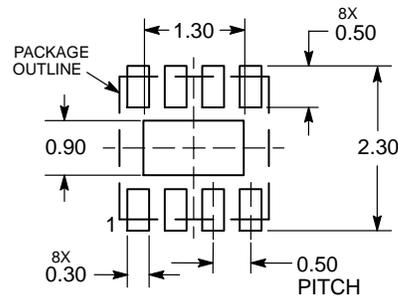
DIMENSIONS: MILLIMETERS

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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MC100LVELT22/D